

N-Channel Enhancement Mode Power MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
60V	70mΩ@10V	3A
	82mΩ@4.5V	

Feature

Trench Technology Power MOSFET

Low $R_{DS(ON)}$

Low Gate Charge

Low Gate Resistance

AEC-Q101 qualified (Automotive grade with suffix "Q".)

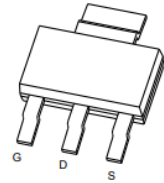
Expsemi electronics

Application

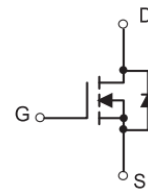
Load Switch

PWM

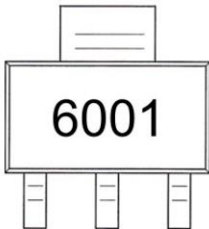
SOT-223



Schematic diagram



MARKING:



6001 = Device Code

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	V_{DS}	60	V
Gate - Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I_D	3	A
Pulsed Drain Current ¹	I_{DM}	10	A
Power Dissipation ³	P_D	2	W
Thermal Resistance from Junction to Ambient ⁴	$R_{\theta JA}$	100	$^{\circ}\text{C/W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}\text{C}$

Electrical Characteristics

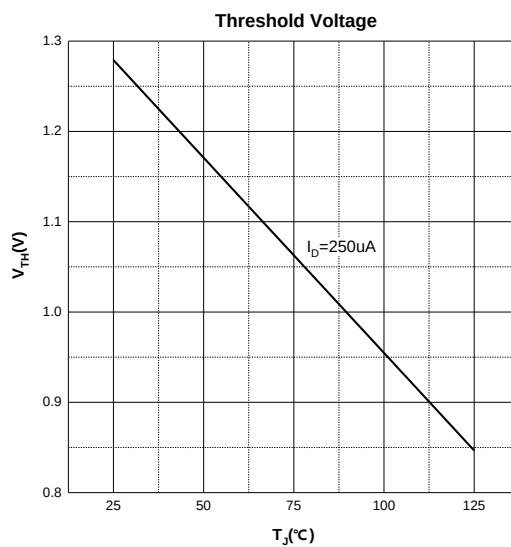
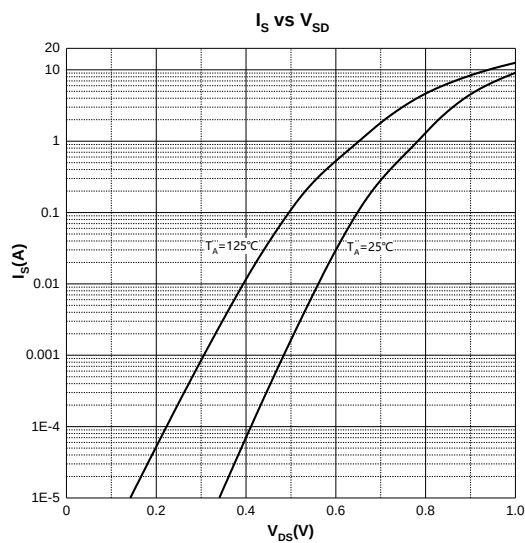
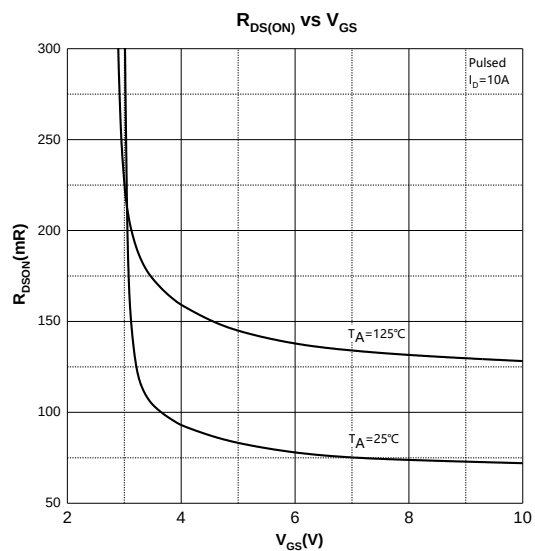
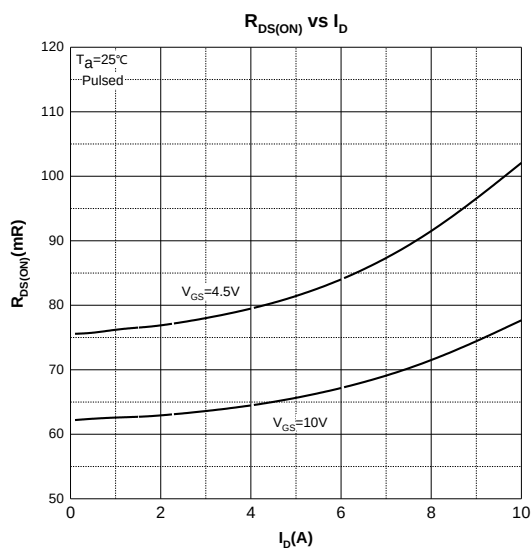
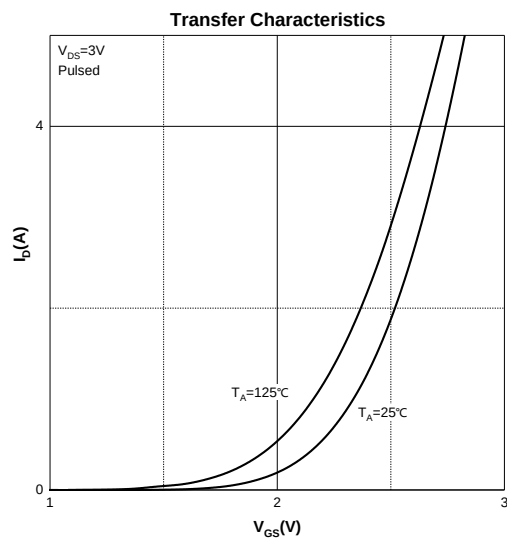
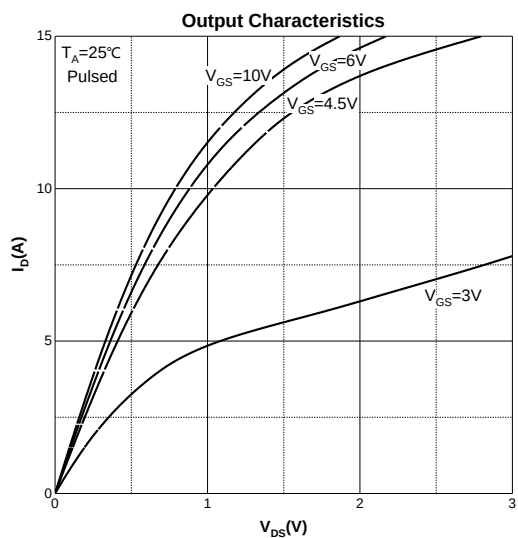
(Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60V, V _{GS} = 0V			1	μA
Gate - Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	nA
On Characteristics ²						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	0.5	1.2	2	V
Drain-source On-resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 3A		70	90	mΩ
		V _{GS} = 4.5V, I _D = 3A		82	125	
Forward Transconductance	g _{FS}	V _{DS} = 15V, I _D = 2A		2.5		S
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} = 30V, V _{GS} = 0V, f = 1MHz		414.3		pF
Output Capacitance	C _{oss}			29.05		
Reverse Transfer Capacitance	C _{rss}			23.06		
Gate Resistance	R _g	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz		2.35		Ω
Switching Characteristics						
Total Gate Charge	Q _g	V _{DS} = 30V, V _{GS} = 4.5V, I _D = 3A		7		nC
Gate-source Charge	Q _{gs}			1.2		
Gate-drain Charge	Q _{gd}			1.5		
Turn-on Delay Time	t _{d(on)}	V _{DD} = 30V, V _{GS} = 10V, R _L = 10Ω R _G = 3Ω		4.7		ns
Turn-on Rise Time	t _r			1.8		
Turn-off Delay Ttime	t _{d(off)}			20		
Turn-off Fall Time	t _f			17.5		
Source - Drain Diode Characteristics						
Diode Forward Voltage ²	V _{SD}	V _{GS} = 0V, I _S = 3A			1.2	V

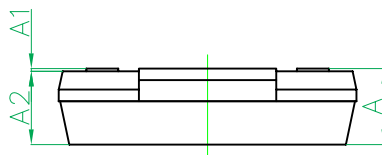
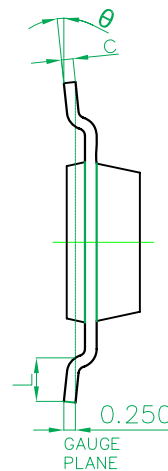
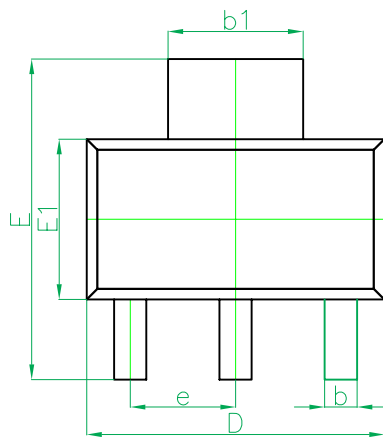
Notes :

- 1.Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
- 2.Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 3.The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ C$.
- 4.Device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ C$.

Typical Characteristic Curves

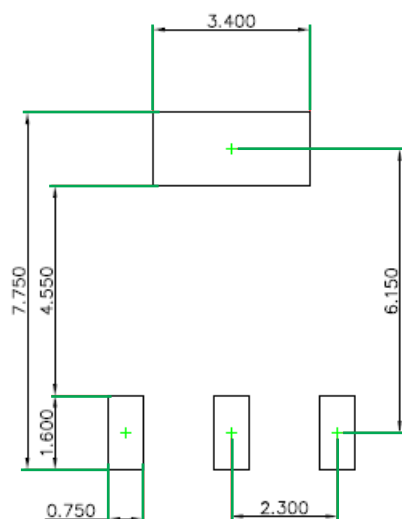


SOT-223 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	—	1.800	—	0.071
A1	0.020	0.100	0.001	0.004
A2	1.500	1.700	0.059	0.067
b	0.660	0.840	0.026	0.033
b1	2.900	3.100	0.114	0.122
c	0.230	0.350	0.009	0.014
D	6.300	6.700	0.248	0.264
E	6.700	7.300	0.264	0.287
E1	3.300	3.700	0.130	0.146
e	2.300(BSC)		0.091(BSC)	
L	0.750	—	0.030	—
θ	0°	10°	0°	10°

SOT-223 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.050\text{mm}$.
3. The pad layout is for reference purposes only.

Ordering information

Device	Package	Reel
EP6001SA	SOT-223	2500/Tape